What is claimed is:

- 1. A hard film formed of a material containing a $(M_{1-x} \mathrm{Si}_x) \; (C_{1-d} \mathrm{N}_d) \; \text{compound, wherein M is at least one of elements}$ in groups 3A, 4A, 5A and 6A and Al, $0.45 \leq x \leq 0.98$ and $0 \leq d \leq 1$, where x, 1-x, d and 1-d are atomic ratios of Si, M, N and C, respectively.
- 2. The hard film according to claim 1, wherein the material further contains 0 in an atomic ration in the range of 0.01 to 0.2.
- 3. The hard film according to claim 1, wherein diffraction peak half width of a (111)-plane of the $(M_{1-x}Si_x)$ ($C_{1-d}N_d$) compound measured by x-ray diffraction is 1.5° or above.
- 4. The hard film according to claim 1, wherein the element M is Cr, Ti or Zr.
- 5. A laminated hard film formed by alternately superposing the hard film according to claim 1, and a hard film formed of a material containing a $(M_{1-x}Si_x)$ $(C_{1-d}N_d)$ compound at a stacking period in the range of 1 to 1000 nm,

wherein M is at least one of elements of groups 3A, 4A, 5A and 6A and Al, $0 \le x \le 0.45$ and $0 \le d \le 1$, where x, 1-x, d and 1-d are atomic ratios of Si, M, N and C, respectively.

6. A hard film formed of a material containing a $(M_{1-x}Si_x)\;(C_{1-d}N_d)\;\;\text{compound on a substrate,}$

wherein M is at least one of elements of groups 3A, 4A, 5A and 6A and Al, the most inner portion of the hard film contiguous with the substrate meets $0 \le x \le 0.45$ and $0 \le d \le 0.45$

1, where x, 1-x, d and 1-d are atomic ratios of Si, M, N and C, respectively, the most outer portion of the hard film meets $0.45 \le x \le 0.98$ and $0 \le d \le 1$, where x, 1-x, d and 1-d are atomic ratios of Si, M, N and C, respectively, and outer portion of the hard film has higher Si atomic ratio x.